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(54) **SEMICONDUCTOR INTEGRATED CIRCUIT DEVICE**

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(57) **ABSTRACT**

An IO cell includes an output circuit having an ESD protection diode, a protective resistance, and an output transistor. The protective resistance is constituted by a plurality of resistor elements formed in a first interconnect layer that is formed in an interconnect process (back end of line (BEOL)). The resistor elements are connected to interconnects formed in a second interconnect layer through vias. In the second interconnect layer, first power supply lines supplying first power are formed above the ESD protection diode. The first power supply lines have overlaps at positions in the X direction with the resistor elements.